ABSTRACT OF THE DISCLOSURE

A method of testing a mask pattern, includes applying optical proximity-effect compensation to a first pattern to be tested and to be formed onto a mask layer, to thereby form a mask pattern of the mask layer, dividing the first pattern into a plurality of areas in accordance with a second pattern to be formed onto another mask layer, determining sampling points on an edge of the first pattern, determining a test standard for each of the areas, simulating a resist pattern formed on a resist by exposing the resist to a light through the mask pattern, and checking whether a dimensional gap between the first pattern and the resist pattern at each of the sampling points is within a test standard associated with an area to which each of the sampling points belongs, wherein test standards for first and second areas among the areas are different from each other.